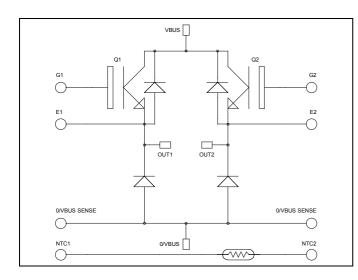
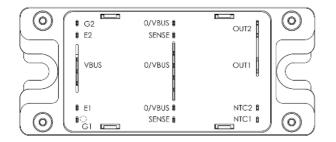


# Dual Buck Chopper NPT IGBT Power Module





# $V_{CES} = 1200 V$

APTGF75DSK120TG

# $I_C = 75A$ @ $Tc = 80^{\circ}C$

#### Application

- AC and DC motor control
- Switched Mode Power Supplies

#### Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
  - Very low stray inductance
    - Symmetrical design
    - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

#### Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS compliant

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_c = 25^{\circ}C$	100	
I <sub>C</sub>	Continuous Conector Current	$T_c = 80^{\circ}C$	75	А
I <sub>CM</sub>	Pulsed Collector Current	$T_c = 25^{\circ}C$	150	
V <sub>GE</sub>	Gate – Emitter Voltage		±20	V
P <sub>D</sub>	Maximum Power Dissipation	$T_c = 25^{\circ}C$	500	W
RBSOA	Continuous Collector Current Pulsed Collector Current Gate – Emitter Voltage Maximum Power Dissipation	$T_j = 150^{\circ}C$	150A @ 1200V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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### All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

# **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
т	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_j = 25^{\circ}C$			250	۸
I <sub>CES</sub>		$V_{CE} = 1200V$	$T_j = 125^{\circ}C$			500	μA
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		3.2	3.7	V
V <sub>CE(sat)</sub>		$I_{\rm C} = 75 {\rm A}$ $T_{\rm j} = 125^{\circ} {\rm C}$	$T_j = 125^{\circ}C$		3.9		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2.5 \text{ mA}$		4.5		6.5	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = \pm 20 V, V_{CE} = 0 V$				±500	nA

## **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			5.1		
Coes	Output Capacitance				0.7		nF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz			0.4		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C)			120		
Tr	Rise Time	$V_{GE} = 15V$			50		
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 75A$ $R_{G} = 7.5\Omega$			310		ns
$T_{\rm f}$	Fall Time				20		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switch	ning (125°C)		130		
Tr	Rise Time	$V_{GE} = 15V$			60		
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 75A$	$V_{Bus} = 600V$		360		ns
$T_{\rm f}$	Fall Time	$R_{\rm G} = 7.5\Omega$			30		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 600V$	$T_j = 125^{\circ}C$		9		mI
E <sub>off</sub>	Turn-off Switching Energy	$I_{C} = 75A$ $R_{G} = 7.5\Omega$	$T_j = 125^{\circ}C$		4		mJ

### **Diode ratings and characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			1200			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_j = 25^{\circ}C$			250	μΑ
I <sub>F</sub>	DC Forward Current		$T_j = 125^{\circ}C$ $Tc = 70^{\circ}C$		100	500	А
	Diode Forward Voltage	$I_F = 100A$			2.0	2.5	
$\mathbf{V}_{\mathrm{F}}$		$I_F = 200A$			2.3		V
		$I_{\rm F} = 100 {\rm A}$	$T_{j} = 125^{\circ}C$		1.8		
ť	$t_{rr}$ Reverse Recovery Time $I_F = 100A$ $Q_{rr}$ Reverse Recovery Charge $i/dt = 200A/di/dt = 200A/dt $		$T_j = 25^{\circ}C$		420		ns
ι <sub>rr</sub>			$T_j = 125^{\circ}C$		580		115
Orr		$di/dt = 200 A/\mu s$ T	$T_j = 25^{\circ}C$		1.2		μC
κ.Π			$T_{j} = 125^{\circ}C$		5.3		

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# APTGF75DSK120TG

### Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

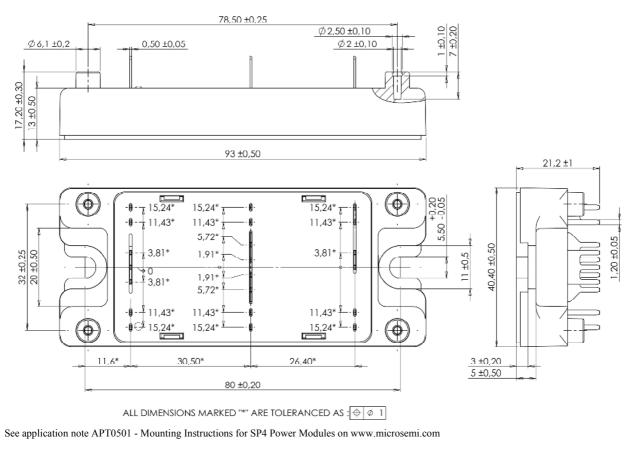
Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K
	n				

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]} R$$

Thermistor temperature  $R_T$ : Thermistor value at T

Symbol	Characteristic		Min	Тур	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance		IGBT			0.25	°C/W
<b>R</b> <sub>th</sub> JC			Diode			0.6	C/ W
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range		-40		150		
T <sub>STG</sub>	Storage Temperature Range		-40		125	°C	
T <sub>C</sub>	Operating Case Temperature		-40		100		
Torque	Mounting torque	To heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

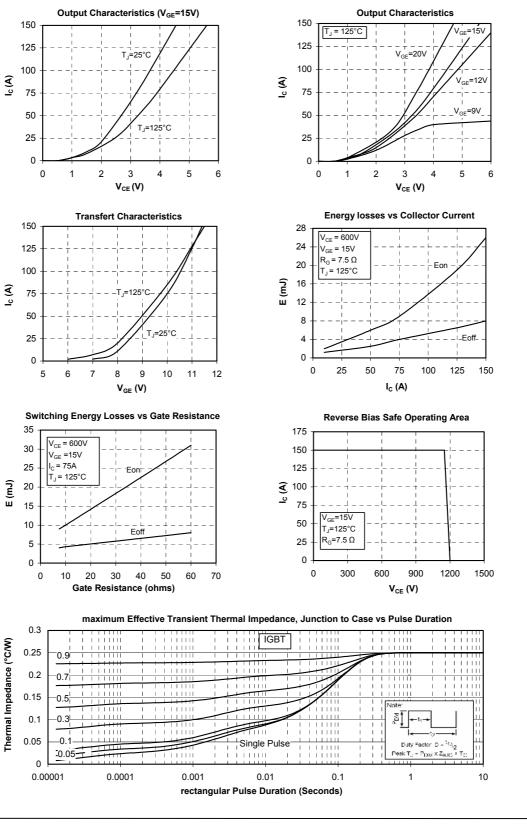
### SP4 Package outline (dimensions in mm)



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#### **Typical Performance Curve**



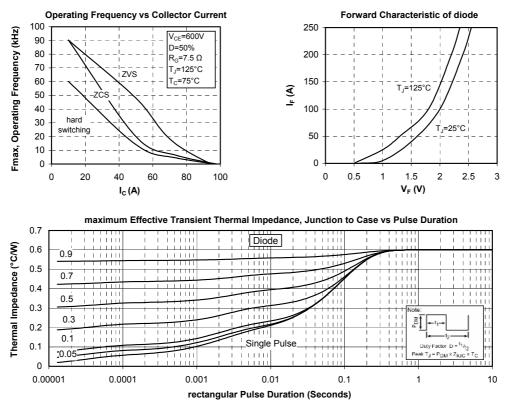
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